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(54) Title: AMMONIUM BORATE CONTAINING COMPOSITIONS FOR STRIPPING RESIDUES FROM SEMICONDUCTOR SUBSTRATES

(57) Abstract

The present invention comprises formulations for stripping wafer residues which originate from a halogen based plasma metal etching followed by oxygen plasma ashing. The formulations contain the following general components (percentages are by weight): an organic amine or mixture of amines 15–60 %, water 20–60 %, ammonium tetraborate or ammonium pentaborate 9–20 %, an optional polar organic solvent 0–15 %.

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